2SC2405, 2SC2406

Silicon NPN epitaxial planer type

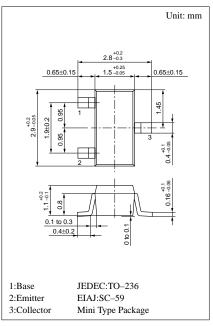
For low-frequency and low-noise amplification Complementary to 2SA1034 and 2SA1035

Features

- Low noise voltage NV.
- High foward current transfer ratio h_{FE}.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit	
Collector to	2SC2405	V	35	V	
base voltage	2SC2406	V_{CBO}	55	V	
Collector to	2SC2405	3.7	35	77	
emitter voltage	2SC2406	V_{CEO}	55	V	
Emitter to base voltage		V_{EBO}	5	V	
Peak collector current		I_{CP}	100	mA	
Collector current		I_{C}	50	mA	
Collector power dissipation		P_{C}	200	mW	
Junction temperature		T_{j}	150	°C	
Storage temperature		T_{stg}	−55 ~ +150	°C	



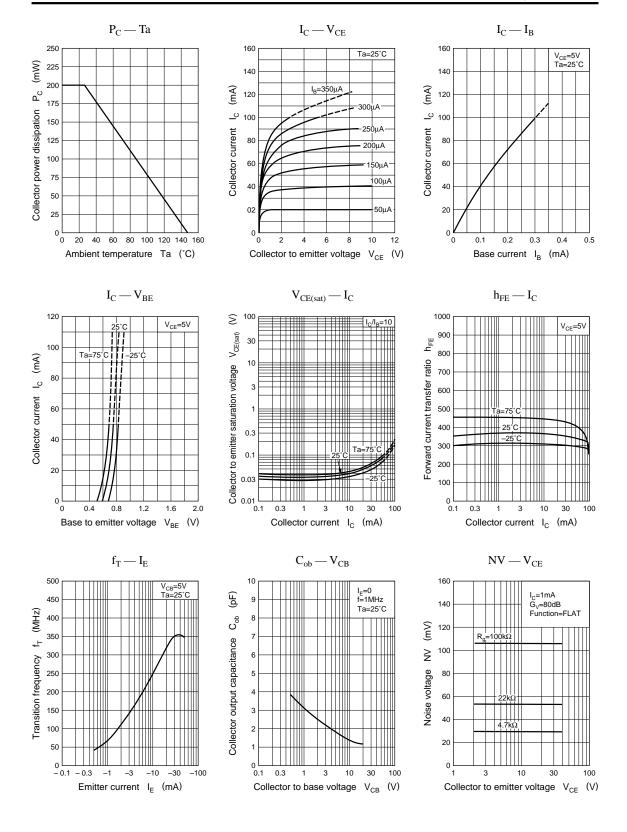
Marking symbol : S(2SC2405) T(2SC2406)

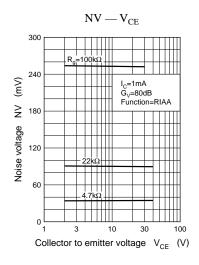
Electrical Characteristics (Ta=25°C)

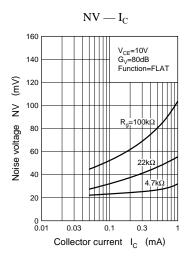
Paramete	er	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I _{CBO}	$V_{CB} = 10V, I_E = 0$			100	nA
		I _{CEO}	$V_{CE} = 10V, I_{B} = 0$			1	μА
Collector to base	2SC2405	17	$I_C = 10\mu A, I_E = 0$	35			V
voltage	2SC2406	$ V_{CBO}$		55			
Collector to emitter	2SC2405		$I_C = 2mA$, $I_B = 0$	35			V
voltage	2SC2406	V _{CEO}		55			
Emitter to base volta	ge	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	5			V
Forward current trans	sfer ratio	h _{FE} *	$V_{CB} = 5V$, $I_E = -2mA$	180		700	
Collector to emitter saturation	on voltage	V _{CE(sat)}	$I_{C} = 100 \text{mA}, I_{B} = 10 \text{mA}$			0.6	V
Base to emitter volta	ge	V _{BE}	$V_{CE} = 1V, I_{C} = 100mA$		0.7	1	V
Transition frequency		f_T	$V_{CB} = 5V, I_E = -2mA, f = 200MHz$		200		MHz
Noise voltage		NV	$V_{CE} = 10V, I_C = 1mA, G_V = 80dB$ $R_g = 100k\Omega, Function = FLAT$		110		mV

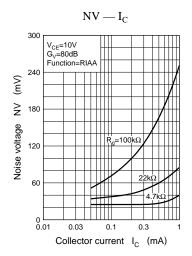
*hFE Rank classification

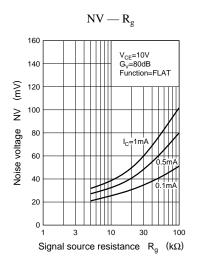
Rank		R	S	T	
h_{FE}		180 ~ 360	260 ~ 520	360 ~ 700	
Marking	2SC2405	SR	SS	ST	
Symbol	2SC2406	TR	TS	TT	

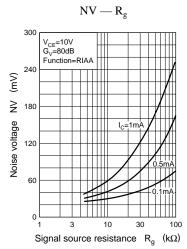












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